

16Mbit SDRAM

512K x 16bit x 2 Banks
Synchronous DRAM
LVTTL

Revision 0.4

April 1998

Revision History**Revision 0.4 (April 17, 1998)**

- Changed DC/AC Test Output Load from 30pF to 50pF in *AC OPERATING TEST CONDITIONS* .
- Changed tOH from 2.5ns to 3ns in KM416S1020C-8/H/L/10 in *AC CHARACTERISTICS* .

Revision 0.3 (April 2, 1998)

- Changed DC/AC Test Output Load from 50pF to 30pF in *AC OPERATING TEST CONDITIONS* .
- Changed tSAC from 6ns to 7ns, tSHZ from 6ns to 7ns @ CL=2 in KM416S1020C-8, tOH from 3ns to 2.5ns in KM416S1020C-8/H/L/10 in *AC CHARACTERISTICS* .

Revision 0.2 (February 1998)

- Input Leakage Currents (Inputs / DQ) are changed(IIL(Inputs) : $\pm 5\mu\text{A}$ to $\pm 1\mu\text{A}$, IIL(DQ) : $\pm 5\mu\text{A}$ to $\pm 1.5\mu\text{A}$).
- Cin to be measured at VDD = 3.3V, TA = 23 °C, f = 1MHz, VREF = 1.4V \pm 200 mV.
- Bining -7 is added.
- Refresh cycle changed 2K/32ms to 4K/64ms.
- AC Operating Condition is changed as defined :
 - VIH(max) = 5.6V AC. The overshoot voltage duration is $\leq 3\text{ns}$.
 - VIL(min) = -2.0V AC. The undershoot voltage duration is $\leq 3\text{ns}$.

Revision 0.1 (November 1997)

- tRDL has changed 10ns to 12ns.

512K x 16Bit x 2 Banks Synchronous DRAM

FEATURES

- JEDEC standard 3.3V power supply
- LVTTTL compatible with multiplexed address
- Dual banks operation
- MRS cycle with address key programs
 - CAS latency (2 & 3)
 - Burst length (1, 2, 4, 8 & Full page)
 - Burst type (Sequential & Interleave)
- All inputs are sampled at the positive going edge of the system clock
- Burst read single-bit write operation
- DQM for masking
- Auto & self refresh
- 64ms refresh period (4K cycle)

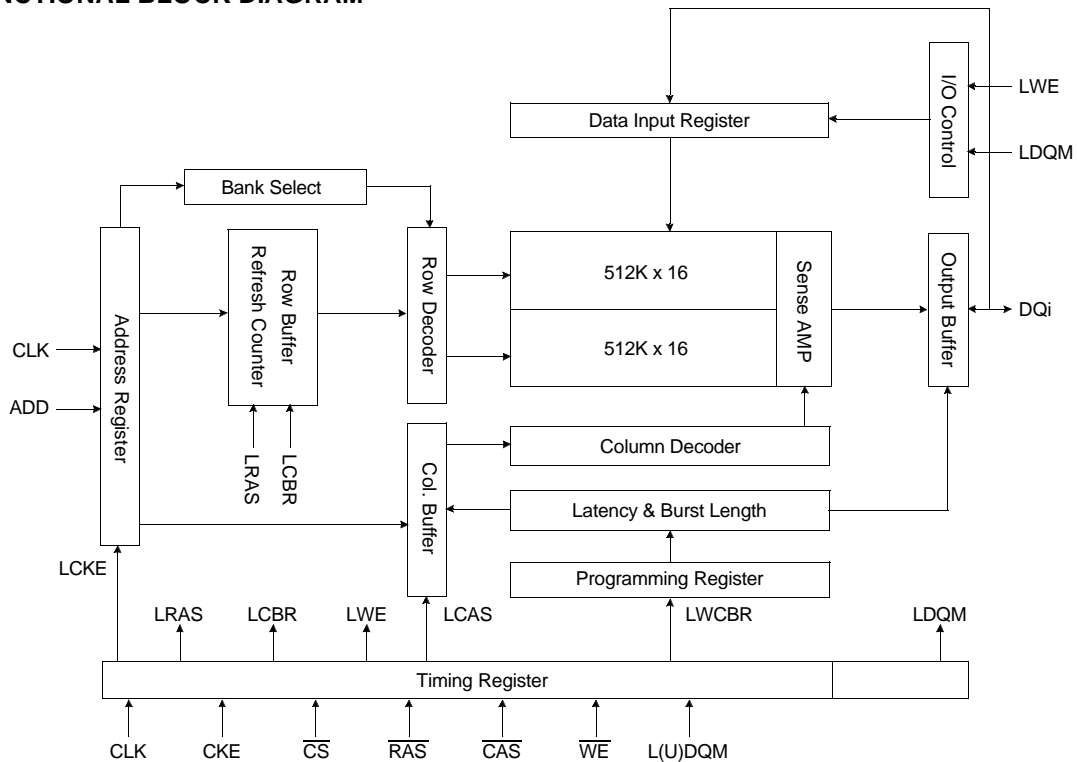
GENERAL DESCRIPTION

The KM416S1020C is 16,777,216 bits synchronous high data rate Dynamic RAM organized as 2 x 524,288 words by 16 bits, fabricated with SAMSUNG 's high performance CMOS technology. Synchronous design allows precise cycle control with the use of system clock I/O transactions are possible on every clock cycle. Range of operating frequencies, programmable burst length and programmable latencies allow the same device to be useful for a variety of high bandwidth, high performance memory system applications.

ORDERING INFORMATION

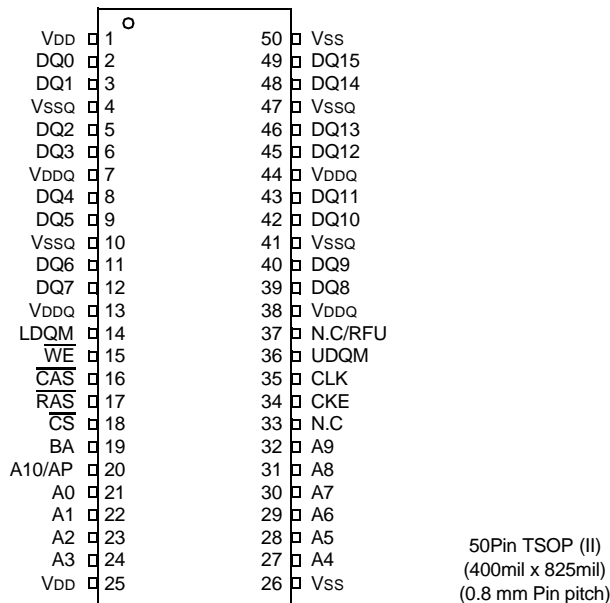
Part No.	Max Freq.	Interface	Package
KM416S1020CT-G/F7	143MHz	LVTTTL	50 TSOP(II)
KM416S1020CT-G/F8	125MHz		
KM416S1020CT-G/FH	100MHz		
KM416S1020CT-G/FL	100MHz		
KM416S1020CT-G/F10	100MHz		

FUNCTIONAL BLOCK DIAGRAM



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PIN CONFIGURATION (Top view)



PIN FUNCTION DESCRIPTION

Pin	Name	Input Function
CLK	System clock	Active on the positive going edge to sample all inputs.
\overline{CS}	Chip select	Disables or enables device operation by masking or enabling all inputs except CLK, CKE and L(U)DQM
CKE	Clock enable	Masks system clock to freeze operation from the next clock cycle. CKE should be enabled at least one cycle prior to new command. Disable input buffers for power down in standby.
A ₀ ~ A _{10/AP}	Address	Row/column addresses are multiplexed on the same pins. Row address : RA ₀ ~ RA ₁₀ , Column address : CA ₀ ~ CA ₇
BA	Bank select address	Selects bank to be activated during row address latch time. Selects bank for read/write during column address latch time.
\overline{RAS}	Row address strobe	Latches row addresses on the positive going edge of the CLK with \overline{RAS} low. Enables row access & precharge.
\overline{CAS}	Column address strobe	Latches column addresses on the positive going edge of the CLK with \overline{CAS} low. Enables column access.
\overline{WE}	Write enable	Enables write operation and row precharge. Latches data in starting from \overline{CAS} , \overline{WE} active.
L(U)DQM	Data input/output mask	Makes data output Hi-Z, t _{SHZ} after the clock and masks the output. Blocks data input when L(U)DQM active.
DQ ₀ ~ 15	Data input/output	Data inputs/outputs are multiplexed on the same pins.
V _{DD} /V _{SS}	Power supply/ground	Power and ground for the input buffers and the core logic.
V _{DDQ} /V _{SSQ}	Data output power/ground	Isolated power supply and ground for the output buffers to provide improved noise immunity.
N.C/RFU	No connection /reserved for future use	This pin is recommended to be left No Connection on the device.

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Voltage on any pin relative to V _{SS}	V _{IN} , V _{OUT}	-1.0 ~ 4.6	V
Voltage on V _{DD} supply relative to V _{SS}	V _{DD} , V _{DDQ}	-1.0 ~ 4.6	V
Storage temperature	T _{STG}	-55 ~ +150	°C
Power dissipation	P _D	1	W
Short circuit current	I _{OS}	50	mA

Note : Permanent device damage may occur if "ABSOLUTE MAXIMUM RATINGS" are exceeded.
 Functional operation should be restricted to recommended operating condition.
 Exposure to higher than recommended voltage for extended periods of time could affect device reliability.

DC OPERATING CONDITIONS

Recommended operating conditions (Voltage referenced to V_{SS} = 0V, T_A = 0 to 70°C)

Parameter	Symbol	Min	Typ	Max	Unit	Note
Supply voltage	V _{DD} , V _{DDQ}	3.0	3.3	3.6	V	
Input logic high voltage	V _{IH}	2.0	3.0	V _{DDQ} +0.3	V	1
Input logic low voltage	V _{IL}	-0.3	0	0.8	V	2
output logic high voltage	V _{OH}	2.4	-	-	V	I _{OH} = -2mA
Output logic low voltage	V _{OL}	-	-	0.4	V	I _{OL} = 2mA
Input leakage current (Inputs)	I _{IL}	-1	-	1	uA	3
Input leakage current (I/O pins)	I _{IL}	-1.5	-	1.5	uA	3,4

Notes : 1. V_{IH} (max) = 5.6V AC. The overshoot voltage duration is ≤ 3ns.
 2. V_{IL} (min) = -2.0V AC. The undershoot voltage duration is ≤ 3ns.
 3. Any input 0V ≤ V_{IN} ≤ V_{DDQ}.
 Input leakage currents include Hi-Z output leakage for all bi-directional buffers with Tri-State outputs.
 4. Dout is disabled, 0V ≤ V_{OUT} ≤ V_{DDQ}.

CAPACITANCE (V_{DD} = 3.3V, T_A = 23°C, f = 1MHz, V_{REF} = 1.4V ± 200 mV)

Pin	Symbol	Min	Max	Unit
Clock	C _{CLK}	2.5	4.0	pF
RAS, CAS, WE, CS, CKE, L(U)DQM	C _{IN}	2.5	5.0	pF
Address	C _{ADD}	2.5	5.0	pF
DQ0 ~ DQ15	C _{OUT}	4.0	6.5	pF

DC CHARACTERISTICS

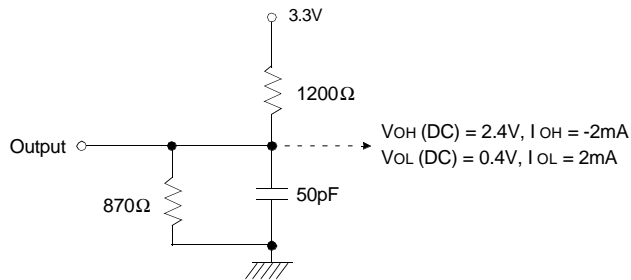
(Recommended operating condition unless otherwise noted, T_A = 0 to 70 °C)

Parameter	Symbol	Test Condition	CAS Latency	Version					Unit	Note
				-7	-8	-H	-L	-10		
Operating current (One bank active)	I _{CC1}	Burst length = 1 t _{RC} ≥ t _{RC} (min) I _{OL} = 0 mA		95	95	90	90	80	mA	1
Precharge standby current in power-down mode	I _{CC2P}	CKE ≤ V _{IL} (max), t _{CC} = 15ns		1					mA	
	I _{CC2PS}	CKE & CLK ≤ V _{IL} (max), t _{CC} = ∞		1						
Precharge standby current in non power-down mode	I _{CC2N}	CKE ≥ V _{IH} (min), \overline{CS} ≥ V _{IH} (min), t _{CC} = 15ns Input signals are changed one time during 30ns		15					mA	
	I _{CC2NS}	CKE ≥ V _{IH} (min), CLK ≤ V _{IL} (max), t _{CC} = ∞ Input signals are stable		4						
Active standby current in power-down mode	I _{CC3P}	CKE ≤ V _{IL} (max), t _{CC} = 15ns		2					mA	
	I _{CC3PS}	CKE & CLK ≤ V _{IL} (max), t _{CC} = ∞		1						
Active standby current in non power-down mode (One bank active)	I _{CC3N}	CKE ≥ V _{IH} (min), \overline{CS} ≥ V _{IH} (min), t _{CC} = 15ns Input signals are changed one time during 30ns		25					mA	
	I _{CC3NS}	CKE ≥ V _{IH} (min), CLK ≤ V _{IL} (max), t _{CC} = ∞ Input signals are stable		15						
Operating current (Burst mode)	I _{CC4}	I _{OL} = 0 mA Page burst 2Banks activated t _{CCD} = 2CLKs	3	140	130	115	115	115	mA	1
			2	100	100	115	100	100		
Refresh current	I _{CC5}	t _{RC} ≥ t _{RC} (min)		90	90	90	90	80	mA	2
Self refresh current	I _{CC6}	CKE ≤ 0.2V		1					mA	3
				250						

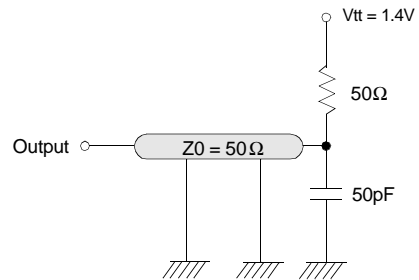
- Notes :**
1. Measured with outputs open.
 2. Refresh period is 64ms.
 3. KM416S1020CT-G**
 4. KM416S1020CT-F**

AC OPERATING TEST CONDITIONS ($V_{DD} = 3.3V \pm 0.3V$, $T_A = 0$ to $70^\circ C$)

Parameter	Value	Unit
AC input levels (V_{ih}/V_{il})	2.4/0.4	V
Input timing measurement reference level	1.4	V
Input rise and fall time	$t_r/t_f = 1/1$	ns
Output timing measurement reference level	1.4	V
Output load condition	See Fig. 2	



(Fig. 1) DC output load circuit



(Fig. 2) AC output load circuit

OPERATING AC PARAMETER

(AC operating conditions unless otherwise noted)

Parameter	Symbol	Version					Unit	Note
		-7	-8	-H	-L	-10		
Row active to row active delay	$t_{RRD}(\min)$	14	16	20	20	20	ns	1
\overline{RAS} to \overline{CAS} delay	$t_{RCD}(\min)$	21	20	20	20	26	ns	1
Row precharge time	$t_{RP}(\min)$	21	20	20	20	26	ns	1
Row active time	$t_{RAS}(\min)$	49	48	50	50	50	ns	1
	$t_{RAS}(\max)$	100					us	
Row cycle time	$t_{RC}(\min)$	70	68	70	70	80	ns	1
Last data in to row precharge	$t_{RDL}(\min)$	7	8	10	10	12	ns	2
Last data in to new col.address delay	$t_{CDL}(\min)$	1					CLK	2
Last data in to burst stop	$t_{BDL}(\min)$	1					CLK	2
Col. address to col. address delay	$t_{CCD}(\min)$	1					CLK	3
Number of valid output data	CAS latency=3	2					ea	4
	CAS latency=2	1						

- Notes :**
1. The minimum number of clock cycles is determined by dividing the minimum time required with clock cycle time and then rounding off to the next higher integer.
 2. Minimum delay is required to complete write.
 3. All parts allow every cycle column address change.
 4. In case of row precharge interrupt, auto precharge and read burst stop.

AC CHARACTERISTICS (AC operating conditions unless otherwise noted)

Parameter		Symbol	-7		-8		-H		-L		-10		Unit	Note
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max		
CLK cycle time	CAS latency=3	tcc	7	1000	8	1000	10	1000	10	1000	10	1000	ns	1
	CAS latency=2		12		12		10		12		13			
CLK to valid output delay	CAS latency=3	tsac		6		6		6		6		7	ns	1,2
	CAS latency=2			7		7		6		7		8		
Output data hold time	CAS latency=3	toH	2.5		3		3		3		3		ns	2
	CAS latency=2		2.5		3		3		3		3			
CLK high pulse width		tCH	2.5		3		3		3		3.5		ns	3
CLK low pulse width		tCL	2.5		3		3		3		3.5		ns	3
Input setup time		tSS	2		2		2		2		2.5		ns	3
Input hold time		tSH	1		1		1		1		1		ns	3
CLK to output in Low-Z		tSLZ	1		1		1		1		1		ns	2
CLK to output in Hi-Z	CAS latency=3	tSHZ		6		6		6		6		7	ns	
	CAS latency=2			7		6		6		7		8		

- Notes :**
1. Parameters depend on programmed CAS latency.
 2. If clock rising time is longer than 1ns, (tr/2-0.5)ns should be added to the parameter.
 3. Assumed input rise and fall time (tr & tf) = 1ns.
 If tr & tf is longer than 1ns, transient time compensation should be considered,
 i.e., [(tr + tf)/2-1]ns should be added to the parameter.

FREQUENCY vs. AC PARAMETER RELATIONSHIP TABLE

KM416S1020CT-7

(Unit : Number of clock)

Frequency	CAS Latency	tRC	tRAS	tRP	tRRD	tRCD	tCCD	tCDL	tRDL
		70ns	49ns	21ns	14ns	21ns	7ns	7ns	7ns
143MHz (7.0ns)	3	10	7	3	2	3	1	1	1
125MHz (8.0ns)	3	9	7	3	2	3	1	1	1
100MHz (10.0ns)	3	7	5	3	2	3	1	1	1
83MHz (12.0ns)	2	6	5	2	2	2	1	1	1
75MHz (13.0ns)	2	6	4	2	2	2	1	1	1
66MHz (15.0ns)	2	5	4	2	1	2	1	1	1

KM416S1020CT-8

(Unit : Number of clock)

Frequency	CAS Latency	tRC	tRAS	tRP	tRRD	tRCD	tCCD	tCDL	tRDL
		68ns	48ns	20ns	16ns	20ns	8ns	8ns	8ns
125MHz (8.0ns)	3	9	6	3	2	3	1	1	1
100MHz (10.0ns)	3	7	5	2	2	2	1	1	1
83MHz (12.0ns)	2	6	4	2	2	2	1	1	1
75MHz (13.0ns)	2	6	4	2	2	2	1	1	1
66MHz (15.0ns)	2	5	4	2	2	2	1	1	1

KM416S1020CT-H

(Unit : Number of clock)

Frequency	CAS Latency	tRC	tRAS	tRP	tRRD	tRCD	tCCD	tCDL	tRDL
		70ns	50ns	20ns	20ns	20ns	10ns	10ns	10ns
100MHz (10.0ns)	2	7	5	2	2	2	1	1	1
83MHz (12.0ns)	2	6	5	2	2	2	1	1	1
75MHz (13.0ns)	2	6	4	2	2	2	1	1	1
66MHz (15.0ns)	2	5	4	2	2	2	1	1	1
60MHz (16.7ns)	2	5	3	2	2	2	1	1	1

KM416S1020CT-L

(Unit : Number of clock)

Frequency	CAS Latency	tRC	tRAS	tRP	tRRD	tRCD	tCCD	tCDL	tRDL
		70ns	50ns	20ns	20ns	20ns	10ns	10ns	10ns
100MHz (10.0ns)	3	7	5	2	2	2	1	1	1
83MHz (12.0ns)	2	6	5	2	2	2	1	1	1
75MHz (13.0ns)	2	6	4	2	2	2	1	1	1
66MHz (15.0ns)	2	5	4	2	2	2	1	1	1
60MHz (16.7ns)	2	5	3	2	2	2	1	1	1

KM416S1020CT-10

(Unit : Number of clock)

Frequency	CAS Latency	tRC	tRAS	tRP	tRRD	tRCD	tCCD	tCDL	tRDL
		80ns	50ns	26ns	20ns	26ns	10ns	10ns	12ns
100MHz (10.0ns)	3	8	5	3	2	3	1	1	2
83MHz (12.0ns)	3	7	5	3	2	3	1	1	1
75MHz (13.0ns)	2	7	4	2	2	2	1	1	1
66MHz (15.0ns)	2	6	4	2	2	2	1	1	1
60MHz (16.7ns)	2	5	3	2	2	2	1	1	1

SIMPLIFIED TRUTH TABLE

Command		CKEn-1	CKEn	\overline{CS}	RAS	\overline{CAS}	\overline{WE}	DQM	BA	A ₁₀ /AP	A ₉ - A ₀	Note
Register	Mode register set	H	X	L	L	L	L	X	OP code			1,2
Refresh	Auto refresh	H	H	L	L	L	H	X	X			3
			L								3	
	Self refresh	L	H	L	H	H	H	X	X			3
				H	X	X	X					3
Bank active & row addr.		H	X	L	L	H	H	X	V	Row address		
Read & column address	Auto precharge disable	H	X	L	H	L	H	X	V	L	Column address (A ₀ - A ₇)	4
	Auto precharge enable									H		4,5
Write & column address	Auto precharge disable	H	X	L	H	L	L	X	V	L	Column address (A ₀ - A ₇)	4
	Auto precharge enable									H		4,5
Burst stop		H	X	L	H	H	L	X	X			6
Precharge	Bank selection	H	X	L	L	H	L	X	V	L	X	
	Both banks								X	H		
Clock suspend or active power down	Entry	H	L	H	X	X	X	X	X			
				L	V	V	V					
Precharge power down mode	Exit	L	H	X	X	X	X	X	X			
				L	H	H	H					
	Entry	H	L	H	X	X	X	X	X			
				L	H	H	H					
Exit	L	H	H	X	X	X	X	X				
			L	V	V	V						
DQM		H	X					V	X			7
No operation command		H	X	H	X	X	X	X	X			
				L	H	H	H					

(V=Valid, X=Don't care, H=Logic high, L=Logic low)

Notes : 1. OP Code : Operand code

A₀ ~ A₁₀/AP, BA : Program keys. (@ MRS)

- MRS can be issued only at both banks precharge state.
A new command can be issued after 2 clock cycle of MRS.
- Auto refresh functions are as same as CBR refresh of DRAM.
The automatical precharge without row precharge command is meant by "Auto".
Auto/self refresh can be issued only at both banks precharge state.
- BA : Bank select address.
If "Low" at read, write, row active and precharge, bank A is selected.
If "High" at read, write, row active and precharge, bank B is selected.
If A₁₀/AP is "High" at row precharge, BA is ignored and both banks are selected.
- During burst read or write with auto precharge, new read/write command can not be issued.
Another bank read/write command can be issued after the end of burst.
New row active of the associated bank can be issued at t_{RP} after the end of burst.
- Burst stop command is valid at every burst length.
- DQM sampled at positive going edge of a CLK masks the data-in at the very CLK (Write DQM latency is 0), but makes Hi-Z state the data-out of 2 CLK cycles after. (Read DQM latency is 2)